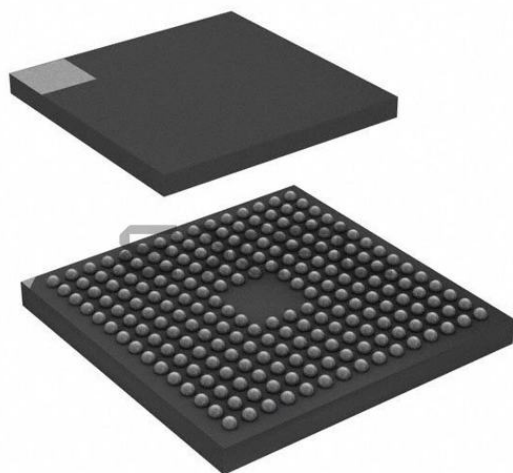




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Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	180MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I ² C, IrDA, LINbus, SAI, SDIO, SPI, UART/USART, USB, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	161
Program Memory Size	2MB (2M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	384K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	216-TFBGA
Supplier Device Package	216-TFBGA (13x13)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f469nih7

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1.1.2 LQFP208 package

Figure 2. Incompatible board design for LQFP208 package

STM32F469xx/479xx LQFP208	138	☐	PC6	STM32F42x/STM32F43x LQFP208	138	☐	PC6
	137	☒	VDDUSB		137	☐	VDD
	136	☐	VSS		136	☐	VSS
	135	☐	PG8		135	☐	PG8
	134	☐	PG7		134	☐	PG7
	133	☐	PG6		133	☐	PG6
	132	☐	PG5		132	☐	PG5
	131	☐	PG4		131	☐	PG4
	130	☐	PG3		130	☐	PG3
	129	☐	PG2		129	☐	PG2
	128	☒	VSSDSI		128	☐	PK2
	127	☒	DSIHOST_D1N		127	☐	PK1
	126	☒	DSIHOST_D1P		126	☐	PK0
	125	☒	VDD12DSI		125	☐	VSS
	124	☒	DSIHOST_CKN		124	☐	VDD
	123	☒	DSIHOST_CKP		123	☐	PJ11
	122	☒	VSSDSI		122	☐	PJ10
	121	☒	DSIHOST_D0N		121	☐	PJ9
	120	☒	DSIHOST_D0P		120	☐	PJ8
	119	☒	VCAPDSI		119	☐	PJ7
	118	☒	VDDDSI		118	☐	PJ6
	117	☐	PD15		117	☐	PD15
	116	☐	PD14		116	☐	PD14

MS38295V1

1. Pins from 118 to 128 and pin 137 are not compatible

The DSI Host main features:

- Compliant with MIPI[®] Alliance standards
- Interface with MIPI[®] D-PHY
- Supports all commands defined in the MIPI[®] Alliance specification for DCS:
 - Transmission of all Command mode packets through the APB interface
 - Transmission of commands in low-power and high-speed during Video Mode
- Supports up to two D-PHY data lanes
- Bidirectional communication and escape mode support through data lane 0
- Supports non-continuous clock in D-PHY clock lane for additional power saving
- Supports Ultra Low-Power mode with PLL disabled
- ECC and Checksum capabilities
- Support for End of Transmission Packet (EoTp)
- Fault recovery schemes
- 3D transmission support
- Configurable selection of system interfaces:
 - AMBA APB for control and optional support for Generic and DCS commands
 - Video Mode interface through LTDC
 - Adapted Command Mode interface through LTDC
- Independently programmable Virtual Channel ID in
 - Video Mode
 - Adapted Command Mode
 - APB Slave

Video Mode interfaces features:

- LTDC interface color coding mappings into 24-bit interface:
 - 16-bit RGB, configurations 1, 2, and 3
 - 18-bit RGB, configurations 1 and 2
 - 24-bit RGB
- Programmable polarity of all LTDC interface signals
- Extended resolutions beyond the DPI standard maximum resolution of 800x480 pixels: maximum resolution is limited by available DSI physical link bandwidth:
 - Number of lanes: 2
 - Maximum speed per lane: 500Mbps

Adapted interface features:

- Support for sending large amounts of data through the *memory_write_start* (WMS) and *memory_write_continue* (WMC) DCS commands
- LTDC interface color coding mappings into 24-bit interface:
 - 16-bit RGB, configurations 1, 2, and 3
 - 18-bit RGB, configurations 1 and 2
 - 24-bit RGB



Table 12. Alternate function (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11	I2C1/2/3	SPI1/2/3/4/5/6	SPI2/3/SAI1	SPI2/3/USART1/2/3	USART6/UART4/5/7/8	CAN1/2/TIM12/13/14/QUADSPI/LCD	QUADSPI/OTG2_HS/OTG1_FS	ETH	FMC/SDIO/OTG2_FS	DCMI/DSI HOST	LCD	SYS
Port H	PH0	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PH1	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PH2	-	-	-	-	-	-	-	-	-	QUADSPI_BK2_IO0	-	ETH_MII_CRS	FMC_SDC KE0	-	LCD_R0	EVENT OUT
	PH3	-	-	-	-	-	-	-	-	-	QUADSPI_BK2_IO1	-	ETH_MII_COL	FMC_SDN E0	-	LCD_R1	EVENT OUT
	PH4	-	-	-	-	I2C2_SCL	-	-	-	-	LCD_G5	OTG_HS_ULPI_NXT	-	-	-	LCD_G4	EVENT OUT
	PH5	-	-	-	-	I2C2_SDA	SPI5_NSS	-	-	-	-	-	-	FMC_SDN WE	-	-	EVENT OUT
	PH6	-	-	-	-	I2C2_SMBA	SPI5_SCK	-	-	-	TIM12_CH1	-	ETH_MII_RXD2	FMC_SDN E1	-	-	EVENT OUT
	PH7	-	-	-	-	I2C3_SCL	SPI5_MISO	-	-	-	-	-	ETH_MII_RXD3	FMC_SDC KE1	DCMI_D9	-	EVENT OUT
	PH8	-	-	-	-	I2C3_SDA	-	-	-	-	-	-	-	FMC_D16	DCMI_HS YNC	LCD_R2	EVENT OUT
	PH9	-	-	-	-	I2C3_SMBA	-	-	-	-	TIM12_CH2	-	-	FMC_D17	DCMI_D0	LCD_R3	EVENT OUT
	PH10	-	-	TIM5_CH1	-	-	-	-	-	-	-	-	-	FMC_D18	DCMI_D1	LCD_R4	EVENT OUT
	PH11	-	-	TIM5_CH2	-	-	-	-	-	-	-	-	-	FMC_D19	DCMI_D2	LCD_R5	EVENT OUT
	PH12	-	-	TIM5_CH3	-	-	-	-	-	-	-	-	-	FMC_D20	DCMI_D3	LCD_R6	EVENT OUT
	PH13	-	-	-	TIM8_CH1_N	-	-	-	-	-	CAN1_TX	-	-	FMC_D21	-	LCD_G2	EVENT OUT
	PH14	-	-	-	TIM8_CH2_N	-	-	-	-	-	-	-	-	FMC_D22	DCMI_D4	LCD_G3	EVENT OUT
	PH15	-	-	-	TIM8_CH3_N	-	-	-	-	-	-	-	-	FMC_D23	DCMI_D11	LCD_G4	EVENT OUT

4 Memory mapping

The memory map is shown in [Figure 21](#).

Figure 21. Memory map

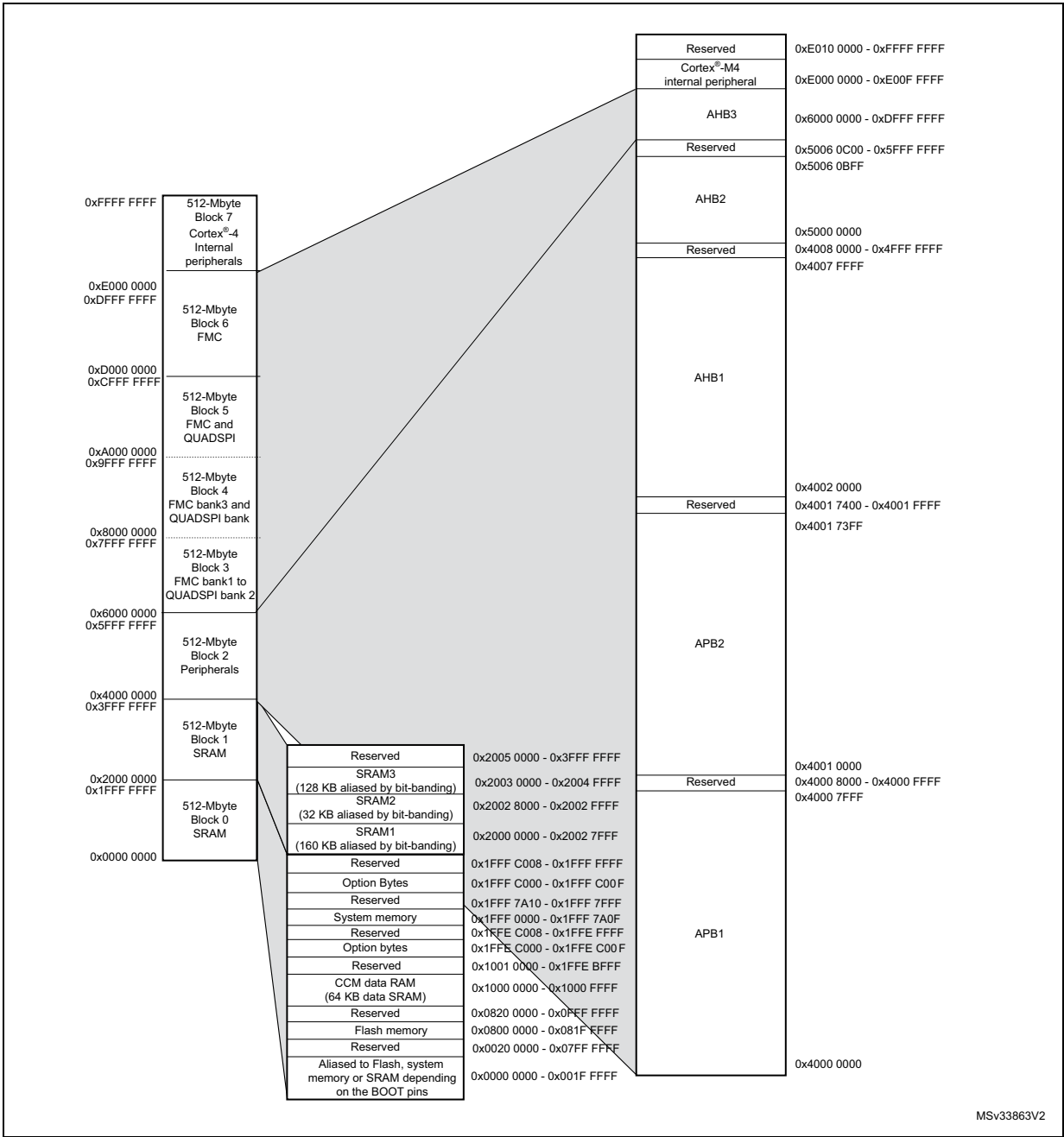


Table 22. Reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{PVD}	Programmable voltage detector level selection	PLS[2:0]=000 (rising edge)	2.09	2.14	2.19	V
		PLS[2:0]=000 (falling edge)	1.98	2.04	2.08	
		PLS[2:0]=001 (rising edge)	2.23	2.30	2.37	
		PLS[2:0]=001 (falling edge)	2.13	2.19	2.25	
		PLS[2:0]=010 (rising edge)	2.39	2.45	2.51	
		PLS[2:0]=010 (falling edge)	2.29	2.35	2.39	
		PLS[2:0]=011 (rising edge)	2.54	2.60	2.65	
		PLS[2:0]=011 (falling edge)	2.44	2.51	2.56	
		PLS[2:0]=100 (rising edge)	2.70	2.76	2.82	
		PLS[2:0]=100 (falling edge)	2.59	2.66	2.71	
		PLS[2:0]=101 (rising edge)	2.86	2.93	2.99	
		PLS[2:0]=101 (falling edge)	2.65	2.84	2.92	
		PLS[2:0]=110 (rising edge)	2.96	3.03	3.10	
		PLS[2:0]=110 (falling edge)	2.85	2.93	2.99	
		PLS[2:0]=111 (rising edge)	3.07	3.14	3.21	
		PLS[2:0]=111 (falling edge)	2.95	3.03	3.09	
$V_{PVDhyst}^{(1)}$	PVD hysteresis	-	-	100	-	mV
$V_{POR/PDR}$	Power-on/power-down reset threshold	Falling edge	1.60	1.68	1.76	V
		Rising edge	1.64	1.72	1.80	
$V_{PDRhyst}^{(1)}$	PDR hysteresis	-	-	40	-	mV
V_{BOR1}	Brownout level 1 threshold	Falling edge	2.13	2.19	2.24	V
		Rising edge	2.23	2.29	2.33	
V_{BOR2}	Brownout level 2 threshold	Falling edge	2.44	2.50	2.56	
		Rising edge	2.53	2.59	2.63	
V_{BOR3}	Brownout level 3 threshold	Falling edge	2.75	2.83	2.88	
		Rising edge	2.85	2.92	2.97	
$V_{BORhyst}^{(1)}$	BOR hysteresis	-	-	100	-	mV
$T_{RSTTEMPO}^{(1)(2)}$	POR reset temporization	-	0.5	1.5	3.0	ms
$I_{RUSH}^{(1)}$	InRush current on voltage regulator power-on (POR or wakeup from Standby)	-	-	160	200	mA
$E_{RUSH}^{(1)}$	InRush energy on voltage regulator power-on (POR or wakeup from Standby)	$V_{DD} = 1.7\text{ V}$, $T_A = 105\text{ °C}$, $I_{RUSH} = 171\text{ mA}$ for $31\text{ }\mu\text{s}$	-	-	5.4	μC

1. Guaranteed by design.

2. The reset temporization is measured from the power-on (POR reset or wakeup from V_{BAT}) to the instant when first instruction is read by the user application code.

Table 33. Peripheral current consumption

Peripheral		I _{DD} (Typ) ⁽¹⁾			Unit
		Scale 1	Scale 2	Scale 3	
AHB1 (up to 180 MHz)	GPIOA	3.16	3.00	2.58	μA/MHz
	GPIOB	2.67	2.62	2.25	
	GPIOC	2.42	2.31	2.10	
	GPIOD	2.22	2.10	1.79	
	GPIOE	2.60	2.48	2.23	
	GPIOF	2.39	2.27	2.08	
	GPIOG	2.27	2.13	1.98	
	GPIOH	2.34	2.20	2.02	
	GPIOI	2.52	2.37	2.17	
	GPIOJ	2.16	2.03	1.86	
	GPIOK	2.20	2.06	1.89	
	OTG_HS+ULPI	36.49	33.89	29.90	
	CRC	0.62	0.55	0.50	
	BKPSRAM	0.83	0.74	0.63	
	DMA1 ⁽²⁾	3.3 x N + 6.8	3 x N + 6.3	2.7 x N + 5.5	
	DMA2 ⁽²⁾	3.4 x N + 5.7	3.1 x N + 5.3	2.8 x N + 4.6	
	DMA2D	33.33	30.66	26.98	
	ETH_MAC ETH_MAC_TX ETH_MAC_RX ETH_MAC_PTP	22.30	20.69	18.19	
AHB2 (up to 180 MHz)	USB_OTG_FS	34.33	31.96	28.35	μA/MHz
	DVCMCI	3.61	3.35	2.98	
	RNG	1.94	1.82	1.61	
AHB3 (up to 180 MHz)	QUADSPI	16.83	15.57	13.83	μA/MHz
	FMC	17.22	15.92	14.00	
Bus matrix ⁽³⁾		12.17	11.19	9.97	μA/MHz

Table 46. MIPI D-PHY AC characteristics LP mode and HS/LP transitions⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{LPX}	Transmitted length of any Low-Power state period	-	50	-	-	ns
$T_{CLK-PREPARE}$	Time that the transmitter drives the Clock Lane LP-00 Line state immediately before the HS-0 Line state starting the HS transmission.	-	38	-	95	
$T_{CLK-PREPARE} + T_{CLK-ZERO}$	Time that the transmitter drives the HS-0 state prior to starting the clock.	-	300	-	-	
$T_{CLK-PRE}$	Time that the HS clock shall be driven by the transmitter prior to any associated Data Lane beginning the transition from LP to HS mode.	-	8	-	-	UI
$T_{CLK-POST}$	Time that the transmitter continues to send HS clock after the last associated Data Lane has transitioned to LP Mode.	-	$62+52*UI$	-	-	ns
$T_{CLK-TRAIL}$	Time that the transmitter drives the HS-0 state after the last payload clock bit of an HS transmission burst.	-	60	-	-	
$T_{HS-PREPARE}$	Time that the transmitter drives the Data Lane LP-00 Line state immediately before the HS-0 Line state starting the HS transmission.	-	$40+4*UI$	-	$85+6*UI$	
$T_{HS-PREPARE} + T_{HS-ZERO}$	$T_{HS-PREPARE}$ + Time that the transmitter drives the HS-0 state prior to transmitting the Sync sequence.	-	$145+10*UI$	-	-	
$T_{HS-TRAIL}$	Time that the transmitter drives the flipped differential state after last payload data bit of a HS transmission burst.	-	Max ($n*8*UI$, $60+n*4*UI$)	-	-	
$T_{HS-EXIT}$	Time that the transmitter drives LP-11 following a HS burst.	-	100	-	-	
T_{REOT}	30%-85% rise time and fall time	-	-	-	35	
T_{EOT}	Transmitted time interval from the start of $T_{HS-TRAIL}$ or $T_{CLK-TRAIL}$ to the start of the LP-11 state following a HS burst.	-	-	-	$105+n*12UI$	

1. Guaranteed based on test during characterization.

Table 60. I/O AC characteristics⁽¹⁾⁽²⁾ (continued)

OSPEEDRy [1:0] bit value ⁽¹⁾	Symbol	Parameter	Conditions	Min	Typ	Max	Unit
11	$f_{\max(\text{IO})\text{out}}$	Maximum frequency ⁽³⁾	$C_L = 30 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	100 ⁽⁴⁾	MHz
			$C_L = 30 \text{ pF}, V_{DD} \geq 1.8 \text{ V}$	-	-	50	
			$C_L = 30 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	42.5	
			$C_L = 10 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	180 ⁽⁴⁾	
			$C_L = 10 \text{ pF}, V_{DD} \geq 1.8 \text{ V}$	-	-	100	
			$C_L = 10 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	72.5	
	$t_{f(\text{IO})\text{out}}/$ $t_{r(\text{IO})\text{out}}$	Output high to low level fall time and output low to high level rise time	$C_L = 30 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	4	ns
			$C_L = 30 \text{ pF}, V_{DD} \geq 1.8 \text{ V}$	-	-	6	
			$C_L = 30 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	7	
			$C_L = 10 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	2.5	
			$C_L = 10 \text{ pF}, V_{DD} \geq 1.8 \text{ V}$	-	-	3.5	
			$C_L = 10 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	4	
-	$t_{\text{EXTI}pw}$	Pulse width of external signals detected by the EXTI controller	-	10	-	-	ns

1. Guaranteed by design.
2. The I/O speed is configured using the OSPEEDRy[1:0] bits. Refer to the STM32F4xx reference manual for a description of the GPIOx_SPEEDR GPIO port output speed register.
3. The maximum frequency is defined in [Figure 40](#).
4. For maximum frequencies above 50 MHz and $V_{DD} > 2.4 \text{ V}$, the compensation cell should be used.

Figure 40. I/O AC characteristics definition

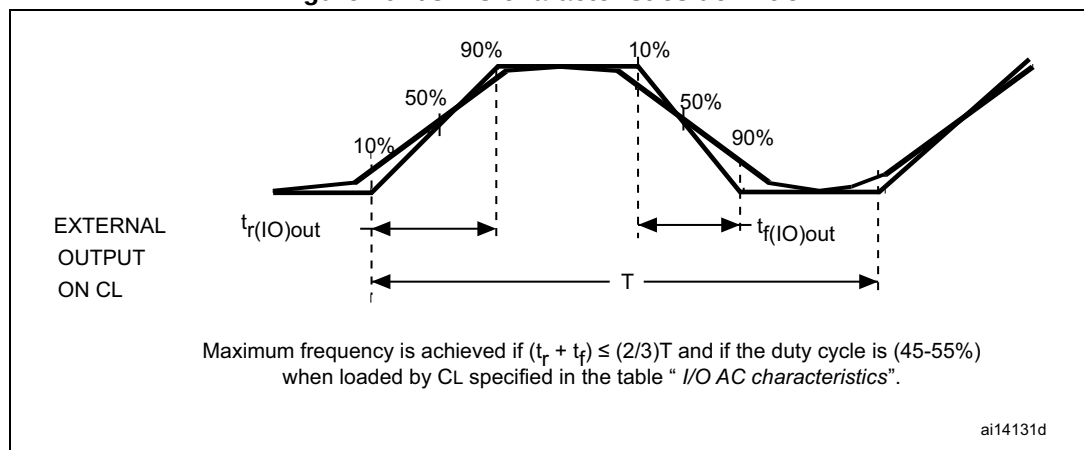
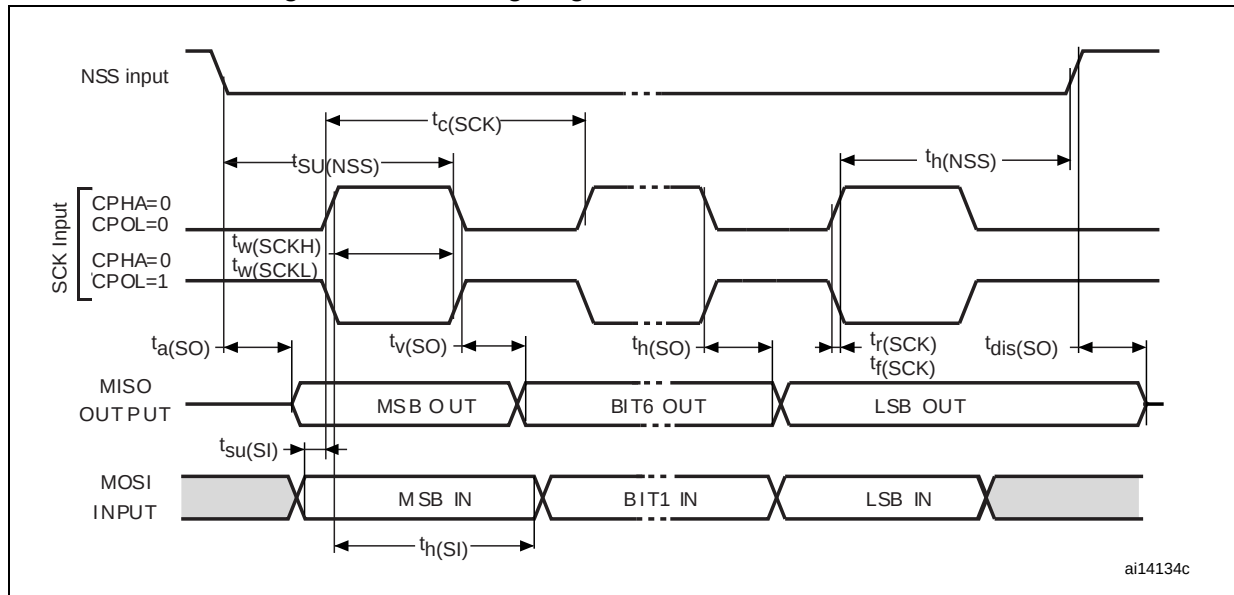
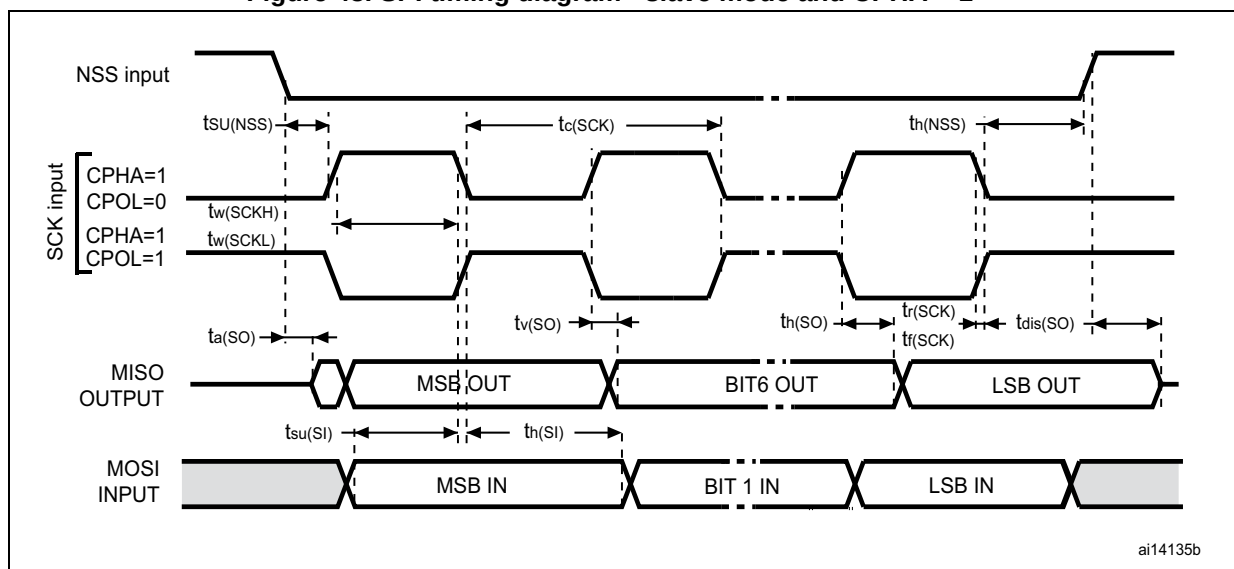


Figure 42. SPI timing diagram - slave mode and CPHA = 0

Figure 43. SPI timing diagram - slave mode and CPHA = 1⁽¹⁾

USB OTG full speed (FS) characteristics

This interface is present in both the USB OTG HS and USB OTG FS controllers.

Table 67. USB OTG full speed startup time

Symbol	Parameter	Max	Unit
$t_{\text{STARTUP}}^{(1)}$	USB OTG full speed transceiver startup time	1	μs

1. Guaranteed by design.

Table 68. USB OTG full speed DC electrical characteristics

Symbol	Parameter	Conditions	Min. ⁽¹⁾	Typ.	Max. ⁽¹⁾	Unit
Input levels	V_{DD}	USB OTG full speed transceiver operating voltage	-	3.0 ⁽²⁾	-	3.6
	$V_{\text{DI}}^{(3)}$	Differential input sensitivity	I(USB_FS_DP/DM, USB_HS_DP/DM)	0.2	-	-
	$V_{\text{CM}}^{(3)}$	Differential common mode range	Includes V_{DI} range	0.8	-	2.5
	$V_{\text{SE}}^{(3)}$	Single ended receiver threshold	-	1.3	-	2.0
Output levels	V_{OL}	Static output level low	R_{L} of 1.5 k Ω to 3.6 V ⁽⁴⁾	-	-	0.3
	V_{OH}	Static output level high	R_{L} of 15 k Ω to V_{SS} ⁽⁴⁾	2.8	-	3.6
R_{PD}	PA11, PA12, PB14, PB15 (USB_FS_DP/DM, USB_HS_DP/DM)	$V_{\text{IN}} = V_{\text{DD}}$	17	21	24	k Ω
	PA9, PB13 (OTG_FS_VBUS, OTG_HS_VBUS)		0.65	1.1	2.0	
R_{PU}	PA12, PB15 (USB_FS_DP, USB_HS_DP)	$V_{\text{IN}} = V_{\text{SS}}$	1.5	1.8	2.1	
	PA9, PB13 (OTG_FS_VBUS, OTG_HS_VBUS)	$V_{\text{IN}} = V_{\text{SS}}$	0.25	0.37	0.55	

1. All the voltages are measured from the local ground potential.
2. The USB OTG full speed transceiver functionality is ensured down to 2.7 V but not the full USB full speed electrical characteristics which are degraded in the 2.7-to-3.0 V V_{DD} voltage range.
3. Guaranteed by design.
4. R_{L} is the load connected on the USB OTG full speed drivers.

Note: When VBUS sensing feature is enabled, PA9 and PB13 should be left at their default state (floating input), not as alternate function. A typical 200 μA current consumption of the sensing block (current to voltage conversion to determine the different sessions) can be observed on PA9 and PB13 when the feature is enabled.

Table 72. Dynamic characteristics: USB ULPI⁽¹⁾

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
t_{SC}	Control in (ULPI_DIR, ULPI_NXT) setup time	-	2.0	-	-	ns
t_{HC}	Control in (ULPI_DIR, ULPI_NXT) hold time	-	1.5	-	-	
t_{SD}	Data in setup time	-	1.0	-	-	
t_{HD}	Data in hold time	-	1.0	-	-	
t_{DC}/t_{DD}	Data/control output delay	$2.7\text{ V} < V_{DD} < 3.6\text{ V}$, $C_L = 20\text{ pF}$	-	7.5	9.0	
		$2.7\text{ V} < V_{DD} < 3.6\text{ V}$, $C_L = 15\text{ pF}$ and $-40 < T < 125^\circ\text{C}$	-	7.5	12.0	
		$1.7\text{ V} < V_{DD} < 3.6\text{ V}$, $C_L = 15\text{ pF}$ and $-40 < T < 90^\circ\text{C}$	-	7.5	11.5	

1. Guaranteed based on test during characterization.

Ethernet characteristics

Unless otherwise specified, the parameters given in [Table 73](#), [Table 74](#) and [Table 75](#) for SMI, RMII and MII are derived from tests performed under the ambient temperature, f_{HCLK} frequency and V_{DD} supply voltage conditions summarized in [Table 17](#), with the following configuration:

- Output speed is set to $OSPEEDRy[1:0] = 10$
- Capacitive load $C = 30\text{ pF}$
- Measurement points are done at CMOS levels: $0.5 V_{DD}$.

Refer to [Section 5.3.20](#) for more details on the input/output characteristics.

[Table 73](#) gives the list of Ethernet MAC signals for the SMI (station management interface) and [Figure 51](#) shows the corresponding timing diagram.

Figure 51. Ethernet SMI timing diagram

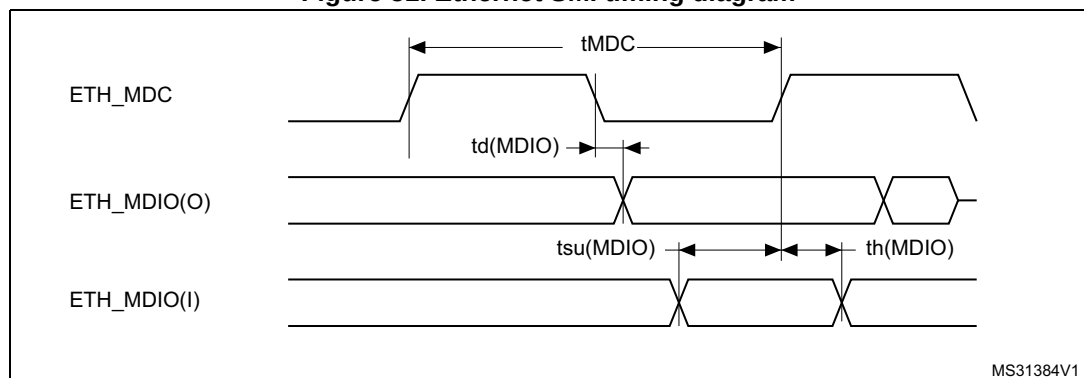


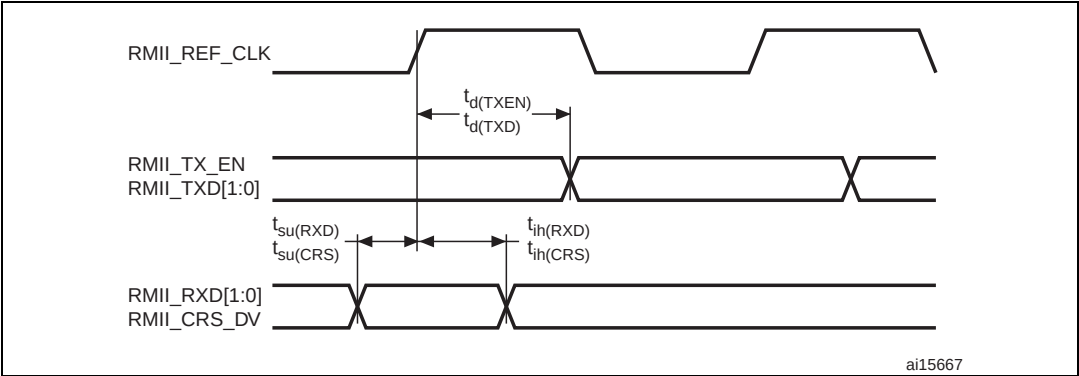
Table 73. Dynamics characteristics: Ethernet MAC signals for SMI⁽¹⁾

Symbol	Parameter	Min	Typ	Max	Unit
t_{MDC}	MDC cycle time(2.38 MHz)	400	400	403	ns
$T_{d(MDIO)}$	Write data valid time	$T_{HCLK} - 1$	T_{HCLK}	$T_{HCLK} + 1.5$	
$t_{su(MDIO)}$	Read data setup time	12.5	-	-	
$t_h(MDIO)$	Read data hold time	0	-	-	

1. Guaranteed based on test during characterization.

[Table 74](#) gives the list of Ethernet MAC signals for the RMI and [Figure 52](#) shows the corresponding timing diagram.

Figure 52. Ethernet RMI timing diagram



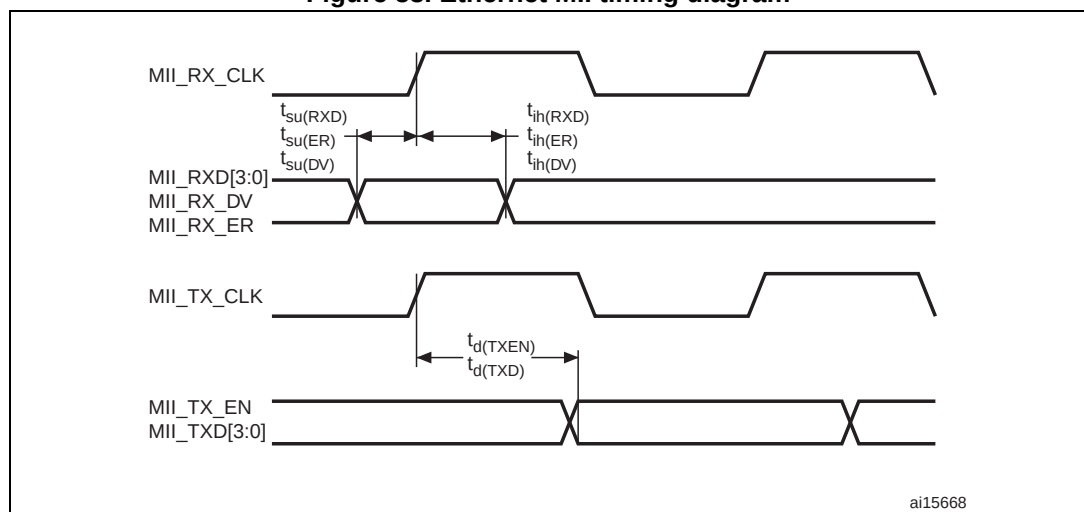
ai15667

Table 74. Dynamics characteristics: Ethernet MAC signals for RMI(1)

Symbol	Parameter	Min	Typ	Max	Unit
$t_{su}(RXD)$	Receive data setup time	2.5	-	-	ns
$t_{ih}(RXD)$	Receive data hold time	2.0	-	-	
$t_{su}(CRS)$	Carrier sense setup time	0.5	-	-	
$t_{ih}(CRS)$	Carrier sense hold time	1.5	-	-	
$t_d(TXEN)$	Transmit enable valid delay time	5.5	6.5	11	
$t_d(TXD)$	Transmit data valid delay time	6.0	6.5	11	

1. Guaranteed based on test during characterization.

[Table 75](#) gives the list of Ethernet MAC signals for MII and [Figure 52](#) shows the corresponding timing diagram.

Figure 53. Ethernet MII timing diagram**Table 75. Dynamics characteristics: Ethernet MAC signals for MII(1)**

Symbol	Parameter	Min	Typ	Max	Unit
$t_{su}(RXD)$	Receive data setup time	1	-	-	ns
$t_{ih}(RXD)$	Receive data hold time	3	-	-	
$t_{su}(DV)$	Data valid setup time	0	-	-	
$t_{ih}(DV)$	Data valid hold time	2.5	-	-	
$t_{su}(ER)$	Error setup time	0	-	-	
$t_{ih}(ER)$	Error hold time	2	-	-	
$t_d(TXEN)$	Transmit enable valid delay time	0	7	13	
$t_d(TXD)$	Transmit data valid delay time	0	7	13	

1. Guaranteed based on test during characterization.

Table 80. ADC dynamic accuracy at $f_{\text{ADC}} = 18 \text{ MHz}$ - limited test conditions⁽¹⁾

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
ENOB	Effective number of bits	$f_{\text{ADC}} = 18 \text{ MHz}$ $V_{\text{DDA}} = V_{\text{REF+}} = 1.7 \text{ V}$ Input Frequency = 20 KHz Temperature = 25 °C	10.3	10.4	-	bits
SINAD	Signal-to-noise and distortion ratio		64	64.2	-	dB
SNR	Signal-to-noise ratio		64	65	-	
THD	Total harmonic distortion		- 67	- 72	-	

1. Guaranteed based on test during characterization.

Table 81. ADC dynamic accuracy at $f_{\text{ADC}} = 36 \text{ MHz}$ - limited test conditions⁽¹⁾

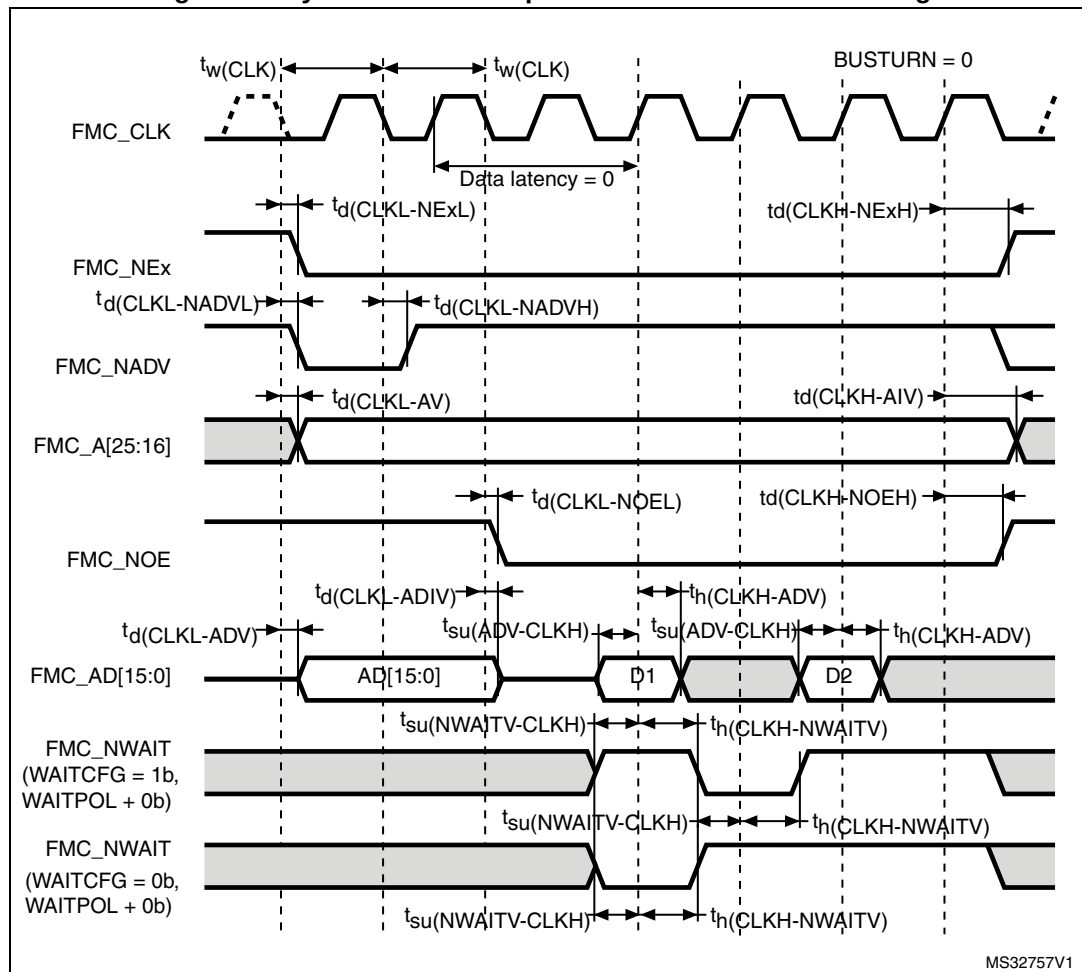
Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
ENOB	Effective number of bits	$f_{\text{ADC}} = 36 \text{ MHz}$ $V_{\text{DDA}} = V_{\text{REF+}} = 3.3 \text{ V}$ Input Frequency = 20 KHz Temperature = 25 °C	10.6	10.8	-	bits
SINAD	Signal-to noise and distortion ratio		66	67	-	dB
SNR	Signal-to noise ratio		64	68	-	
THD	Total harmonic distortion		- 70	- 72	-	

1. Guaranteed based on test during characterization.

Note: ADC accuracy vs. negative injection current: injecting a negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.

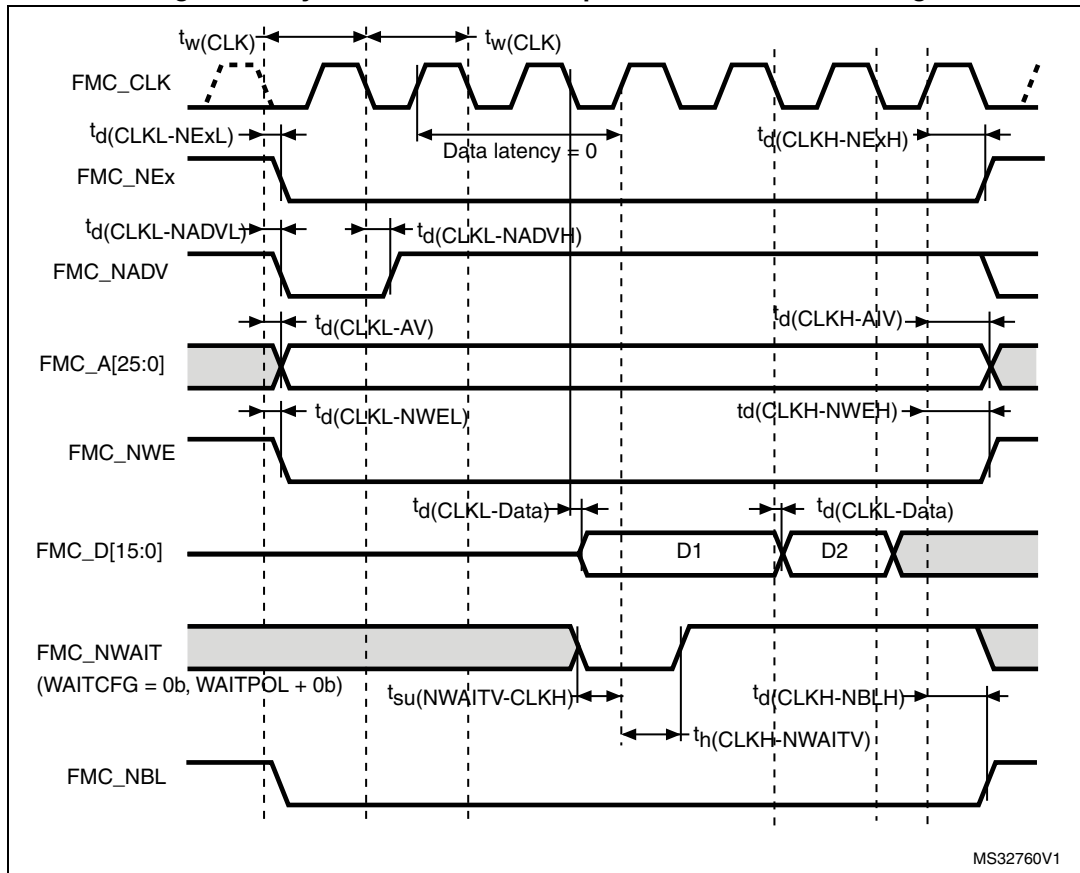
Any positive injection current within the limits specified for $I_{\text{INJ(PIN)}}$ and $\Sigma I_{\text{INJ(PIN)}}$ in [Section 5.3.20](#) does not affect the ADC accuracy.

Figure 63. Synchronous multiplexed NOR/PSRAM read timings



MS32757V1

Figure 66. Synchronous non-multiplexed PSRAM write timings

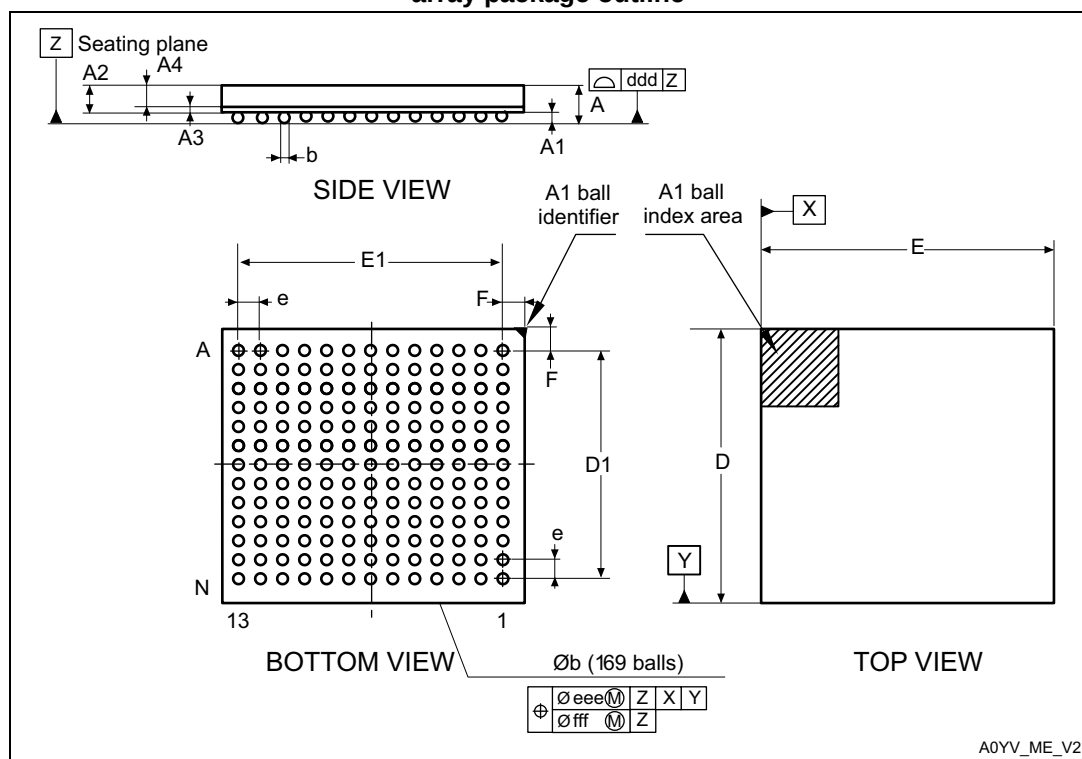
Table 99. Synchronous non-multiplexed PSRAM write timings⁽¹⁾

Symbol	Parameter	Min	Max	Unit
t_{CLK}	FMC_CLK period	$2T_{\text{HCLK}} - 1$	-	ns
$t_{\text{d}}(\text{CLKL-NExL})$	FMC_CLK low to FMC_NEx low ($x=0\dots2$)	-	0.5	
$t_{\text{d}}(\text{CLKH-NExH})$	FMC_CLK high to FMC_NEx high ($x=0\dots2$)	T_{HCLK}	-	
$t_{\text{d}}(\text{CLKL-NADV})$	FMC_CLK low to FMC_NADV low	-	0	
$t_{\text{d}}(\text{CLKL-NADVH})$	FMC_CLK low to FMC_NADV high	0	-	
$t_{\text{d}}(\text{CLKL-AV})$	FMC_CLK low to FMC_Ax valid ($x=16\dots25$)	-	0	
$t_{\text{d}}(\text{CLKH-AIV})$	FMC_CLK high to FMC_Ax invalid ($x=16\dots25$)	0	-	
$t_{\text{d}}(\text{CLKL-NWE})$	FMC_CLK low to FMC_NWE low	-	0	
$t_{\text{d}}(\text{CLKH-NWEH})$	FMC_CLK high to FMC_NWE high	$T_{\text{HCLK}} - 0.5$	-	
$t_{\text{d}}(\text{CLKL-Data})$	FMC_D[15:0] valid data after FMC_CLK low	-	2.5	
$t_{\text{d}}(\text{CLKL-NBL})$	FMC_CLK low to FMC_NBL low	0	-	
$t_{\text{d}}(\text{CLKH-NBLH})$	FMC_CLK high to FMC_NBL high	$T_{\text{HCLK}} - 0.5$	-	
$t_{\text{su}}(\text{NWAIT-CLKH})$	FMC_NWAIT valid before FMC_CLK high	4	-	
$t_{\text{h}}(\text{CLKH-NWAIT})$	FMC_NWAIT valid after FMC_CLK high	0	-	

1. Based on test during characterization.

6.4 UFBGA169 package information

Figure 87. UFBGA169 - 169-pin, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package outline



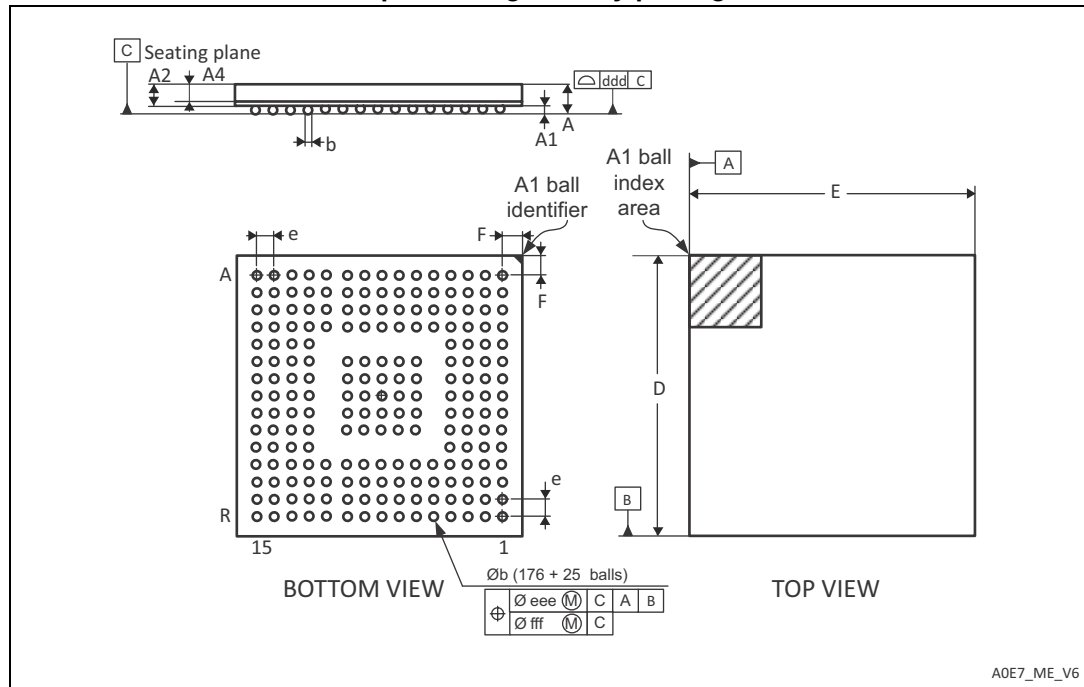
1. Drawing is not in scale.

Table 116. UFBGA169 - 169-pin, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	0.460	0.530	0.600	0.0181	0.0209	0.0236
A1	0.050	0.080	0.110	0.0020	0.0031	0.0043
A2	0.400	0.450	0.500	0.0157	0.0177	0.0197
A3	-	0.130	-	-	0.0051	-
A4	0.270	0.320	0.370	0.0106	0.0126	0.0146
b	0.230	0.280	0.330	0.0091	0.0110	0.0130
D	6.950	7.000	7.050	0.2736	0.2756	0.2776
D1	5.950	6.000	6.050	0.2343	0.2362	0.2382
E	6.950	7.000	7.050	0.2736	0.2756	0.2776
E1	5.950	6.000	6.050	0.2343	0.2362	0.2382
e	-	0.500	-	-	0.0197	-
F	0.450	0.500	0.550	0.0177	0.0197	0.0217

6.6 UFBGA176+25 package information

Figure 92. UFBGA176+25 - 201-ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package outline



1. Drawing is not to scale.

Table 118. UFBGA176+25, - 201-ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	0.460	0.530	0.600	0.0181	0.0209	0.0236
A1	0.050	0.080	0.110	0.0020	0.0031	0.0043
A2	0.400	0.450	0.500	0.0157	0.0177	0.0197
A4	0.270	0.320	0.370	0.0106	0.0126	0.0146
b	0.230	0.280	0.330	0.0091	0.0110	0.0130
D	9.950	10.000	10.050	0.3917	0.3937	0.3957
E	9.950	10.000	10.050	0.3917	0.3937	0.3957
e	-	0.650	-	-	0.0256	-
F	0.400	0.450	0.500	0.0157	0.0177	0.0197
ddd	-	-	0.080	-	-	0.0031
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.